

Supplementary information for

**Multiferroelectricity in two-dimensional Indium Pnictide
optoelectronic materials**

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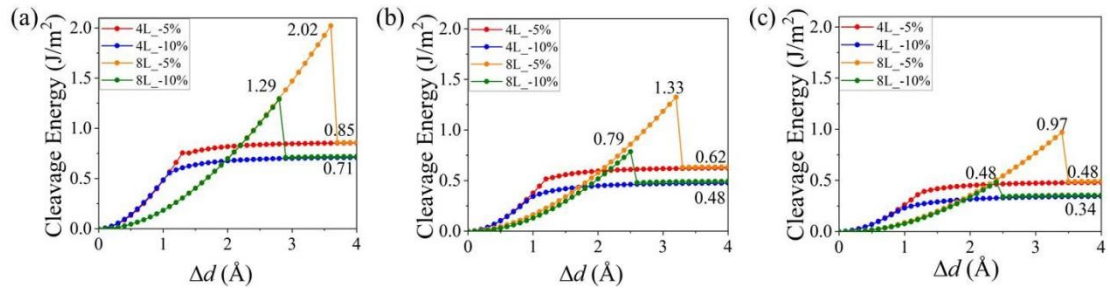


Fig. S1 Cleavage energy for indium pnictides with different strain.

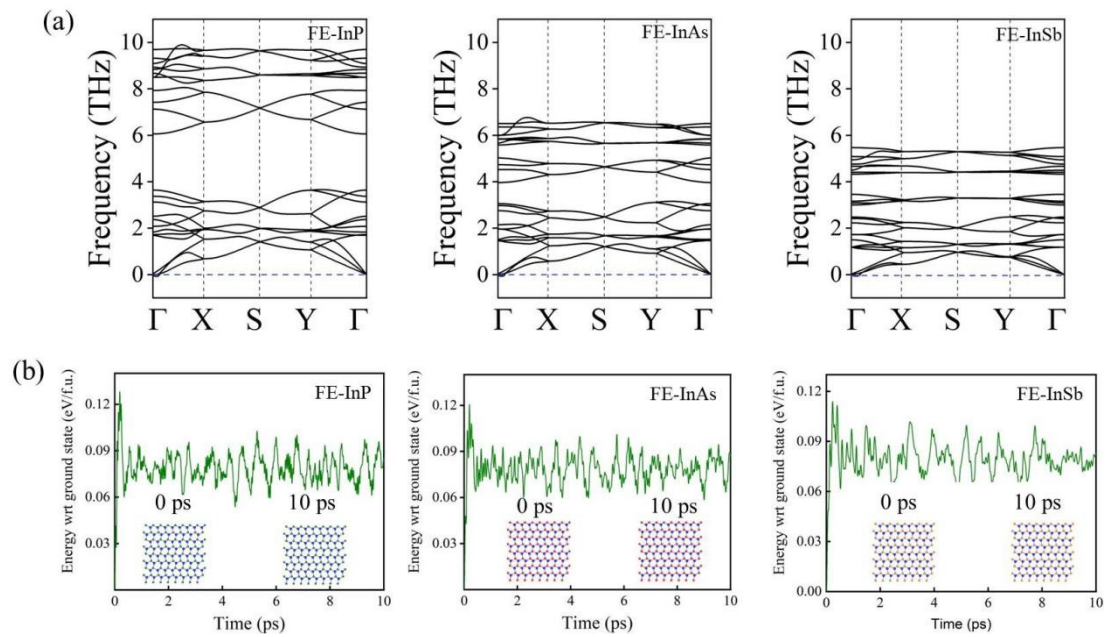


Fig. S2 (a) Phonon spectrum and (b) AIMD simulation for monolayer indium pnictides, which suggests that the monolayer structure is stable with non-imaginary frequency phonon dispersion and no phase change.

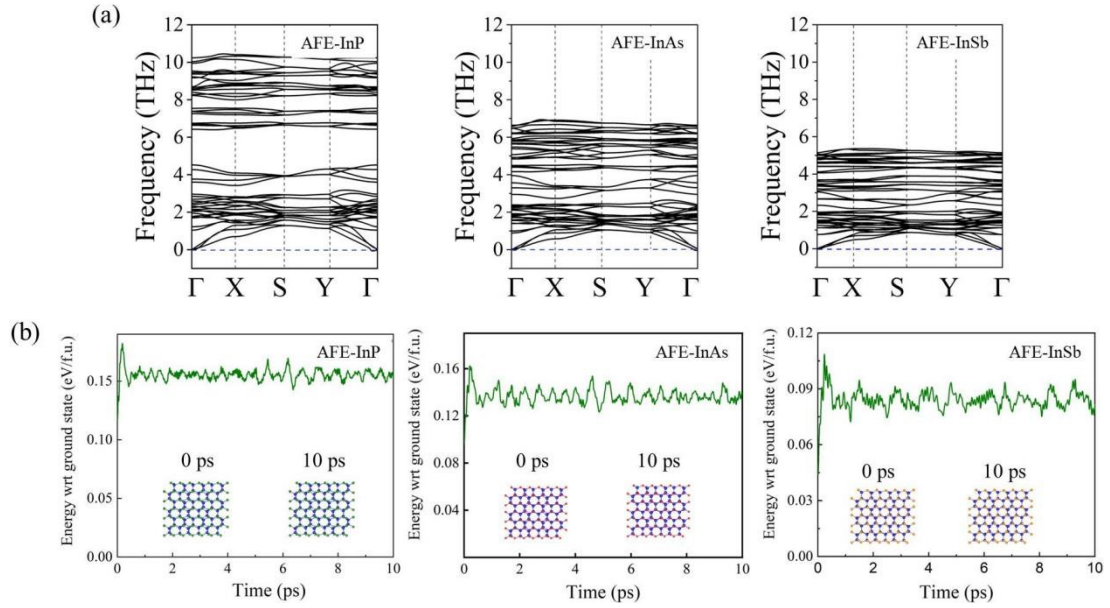


Fig. S3 (a) Phonon spectrum and **(b)** AIMD simulation for AFE indium pnictides, which suggest that the AFE structure is stable with non-imaginary frequency phonon dispersion and no phase change.

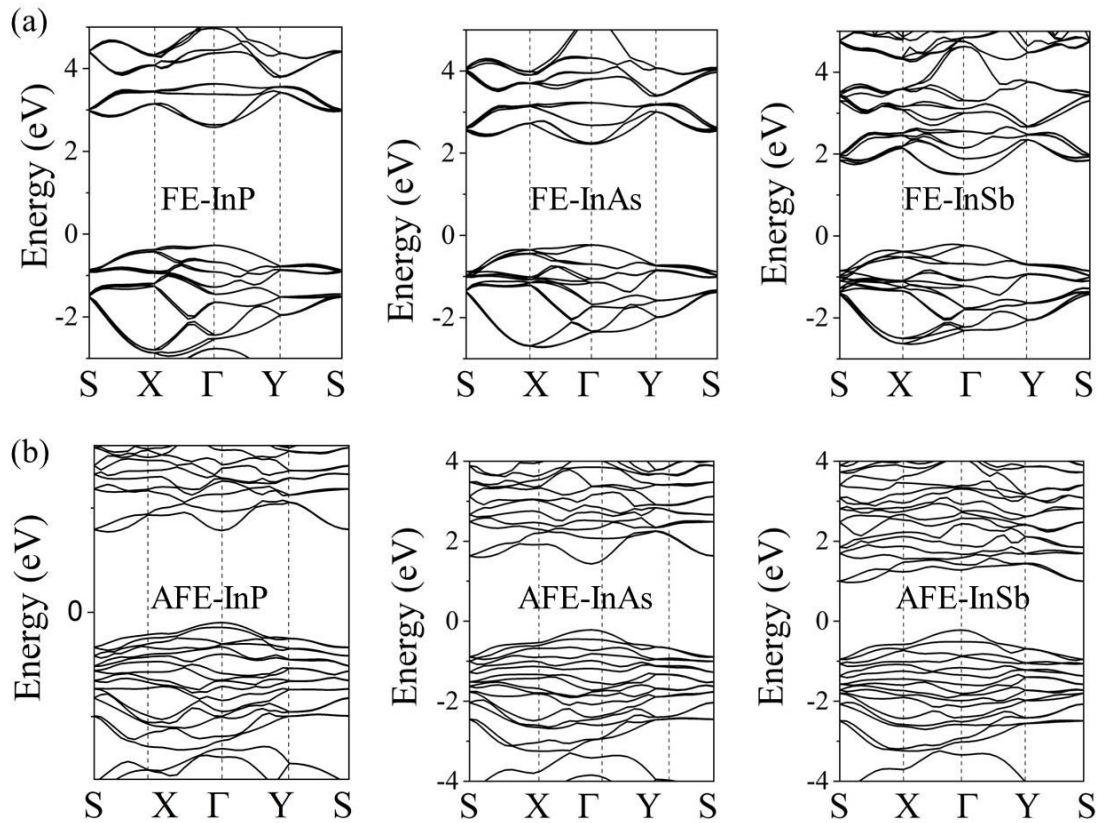


Fig. S4 Band structure of FE (a) and AFE (b) phases of indium pnictides from HSE06+SOC.

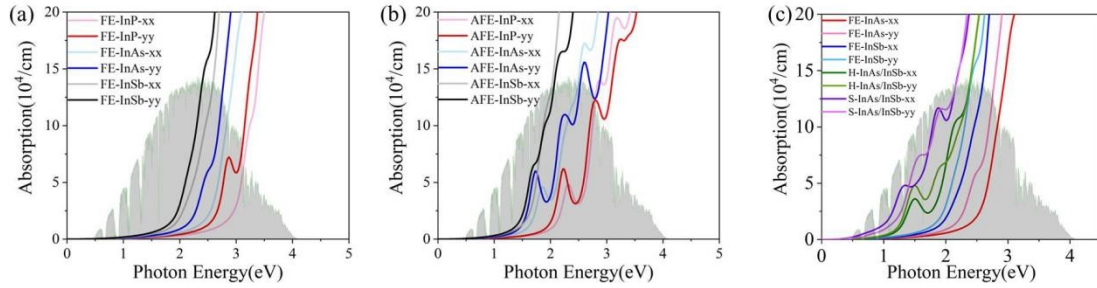


Fig. S5 Optical absorption coefficient of FE (a) and AFE (b) of indium pnictides, (c) heterojunction and superlattice of InAs/InSb phases. The reference air-mass 1.5-solar spectral irradiance is plotted in gray shadow.

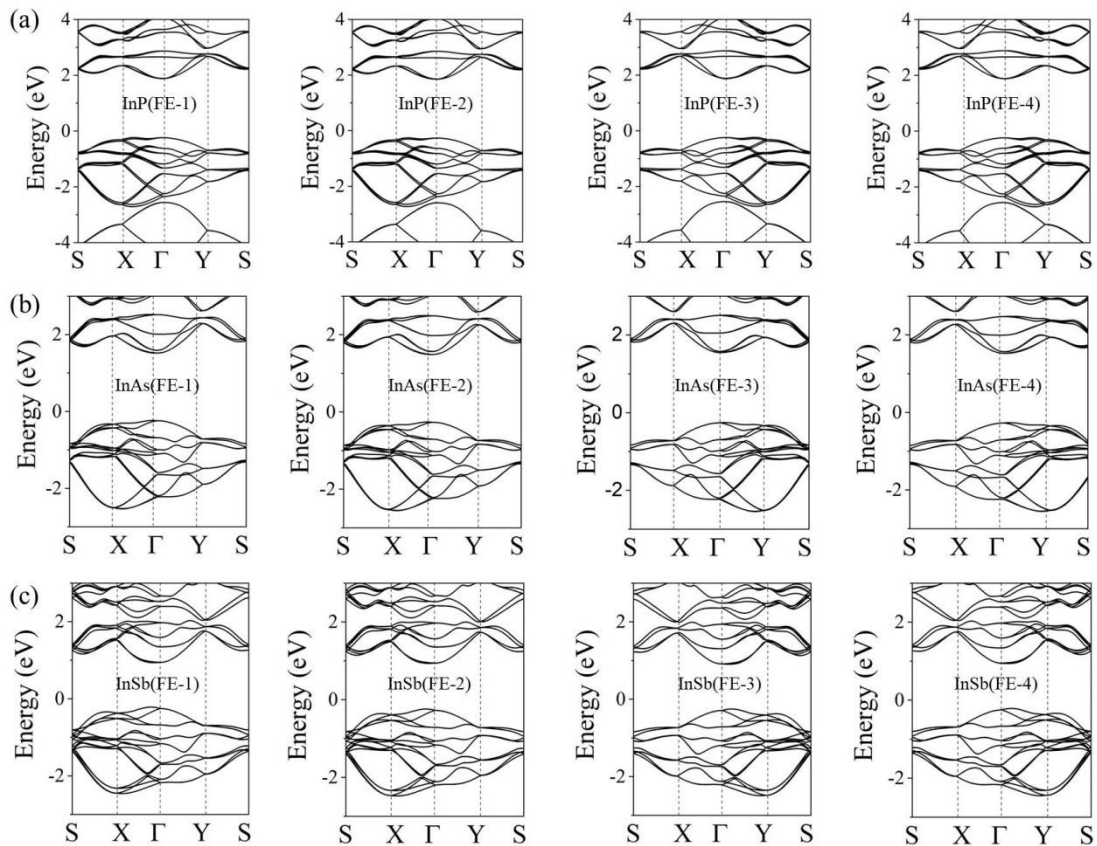


Fig. S6 Electronic band structures with SOC for indium pnictides monolayers with FE ($Pca2_1$) symmetry.

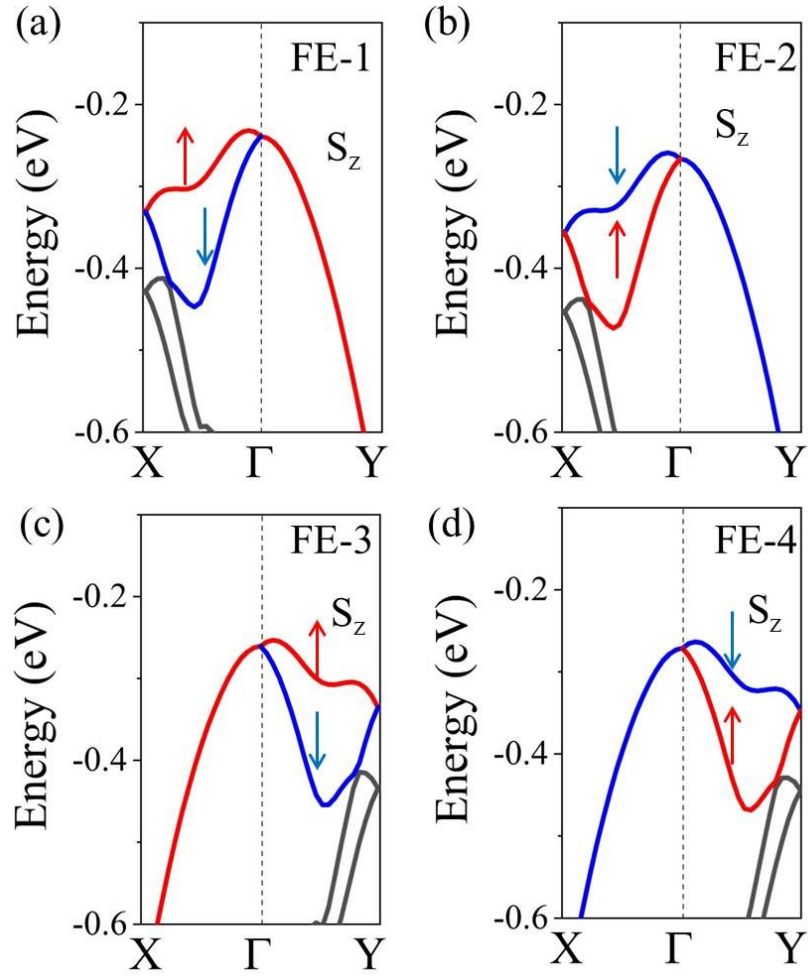


Fig. S7 The highlighted spin-split bands around VBM region of InAs monolayer. The splitting bands along Γ -Y/X (spin degenerate/splitting) and Γ -X/Y (spin degenerate/splitting) high-symmetry lines around VBM for $FE_{A/B}$ phases indicate the anisotropy flipping feature during the FC phase change process. The spin up and down property is inverted accompanied by the FE-1/2 phase change, in which the red and blue arrows indicate S_z (up) and $-S_z$ (down) spin orientation in the momentum space, respectively.

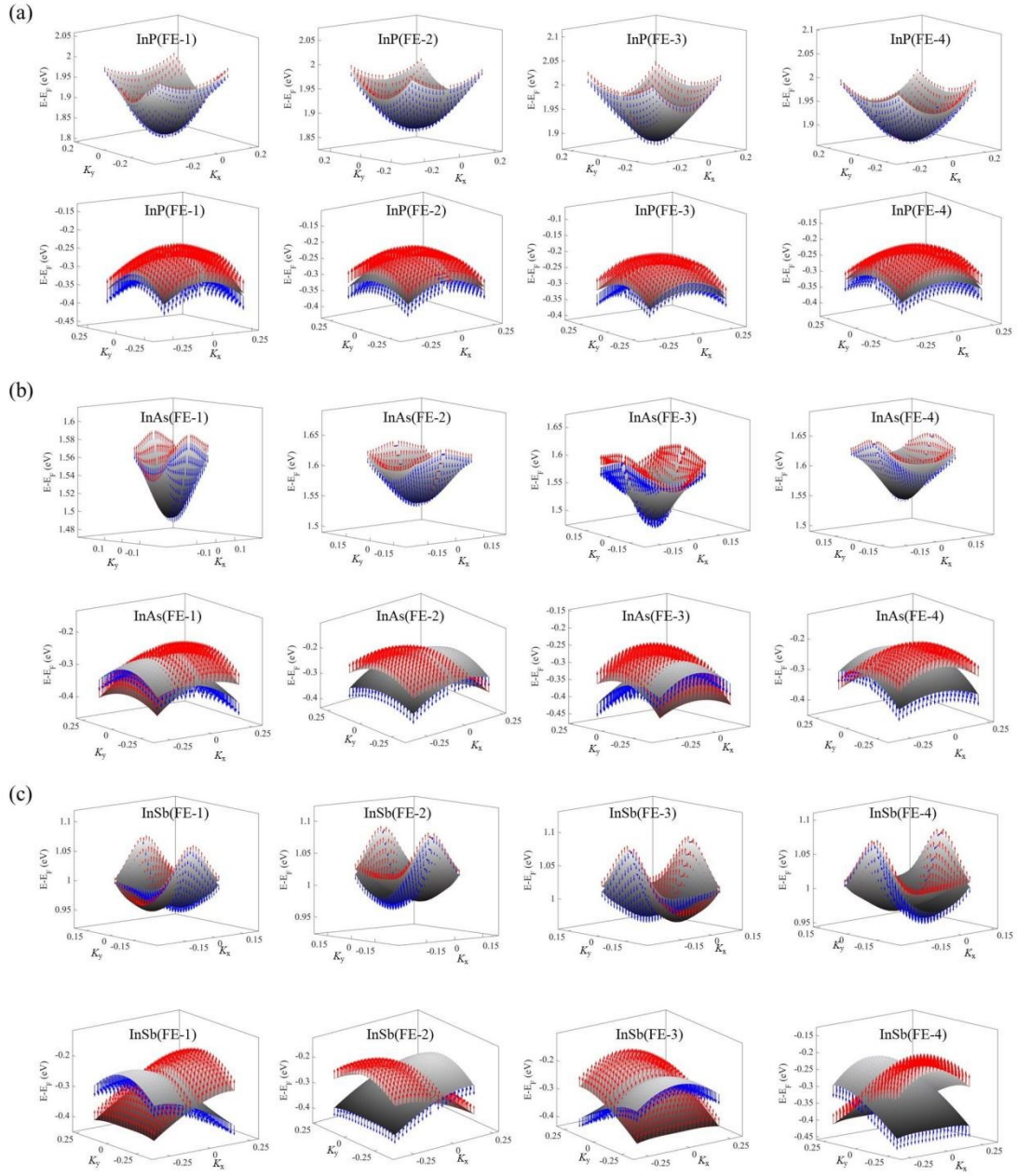


Fig. S8 (a-c) Switchable spin texture projected to the k space for the upper and lower bands of monolayer indium pnictides around CBM and VBM, which is expected by reversing the in-plane ferroelectric polarization.

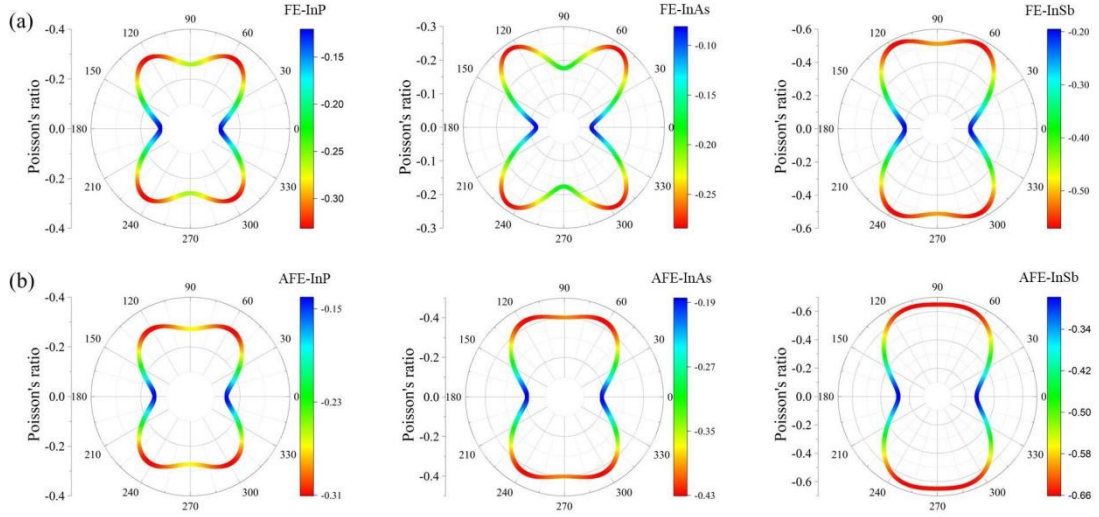


Fig. S9 Anisotropic in-plane NPR response for 2D FE (a) and AFE (b) indium pnictides.

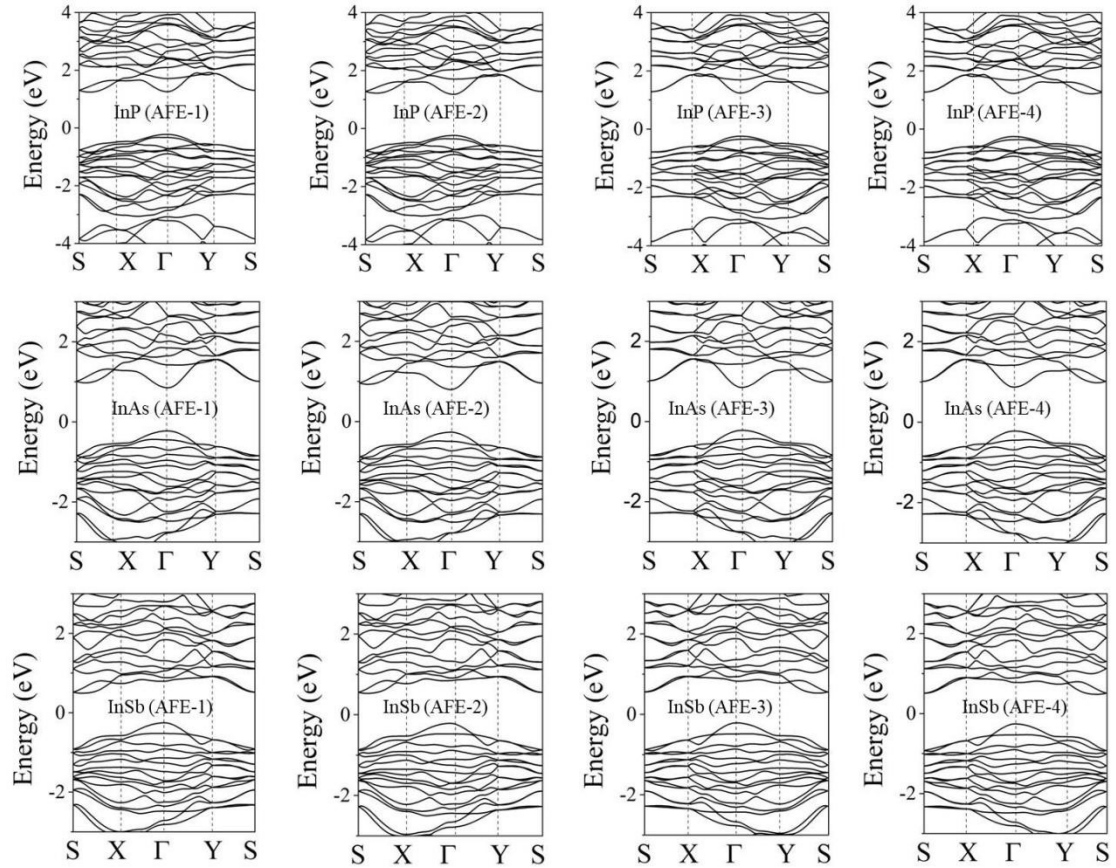


Fig. S10 Electronic band structures with SOC for indium pnictides with AFE ($P2/c$)

symmetry.

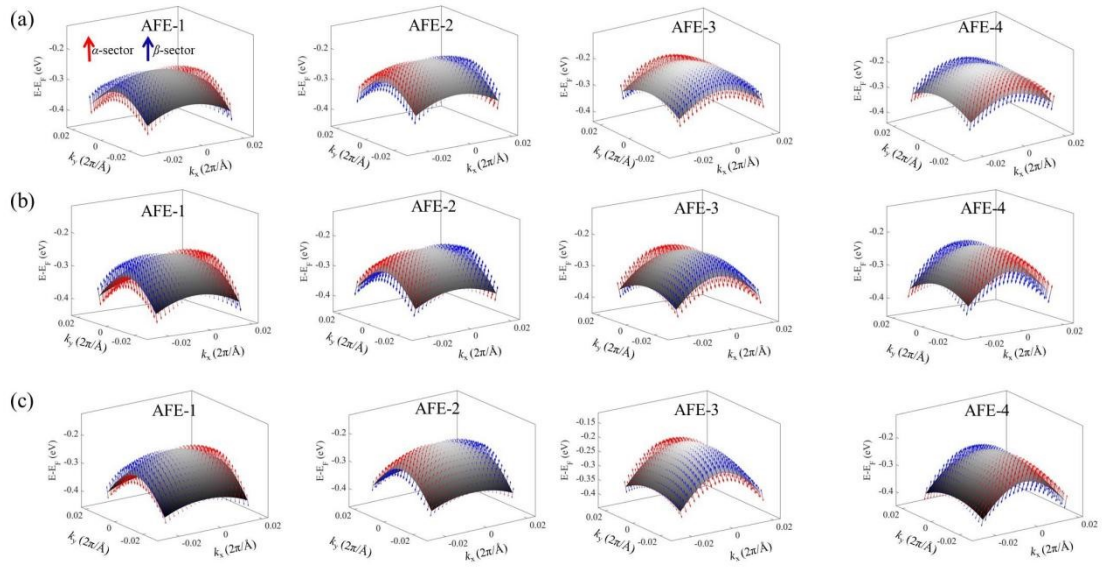


Fig. S11 (a-c) Switchable hidden spin texture projected to the k space for the upper and lower bands of AFE indium pnictides around VBM.